SONY

Diagonal 6mm (Type 1/3) Progressive Scan CCD Image Sensor with Square Pixel for B/W Cameras

Description

The ICX204AL is a diagonal 6mm (Type 1/3) interline CCD solid-state image sensor with a square pixel array and 800K effective pixels. Progressive scan allows all pixels' signals to be output independently. Also, the adoption of high frame rate readout mode supports 60 frames per second. This chip features an electronic shutter with variable charge-storage time which makes it possible to realize full-frame still image without a mechanical shutter. Further, high sensitivity and low dark current are achieved through the adoption of HAD (Hole-Accumulation Diode) sensors.

This chip is suitable for applications such as FA cameras, two-dimensional bar-code reader, etc.

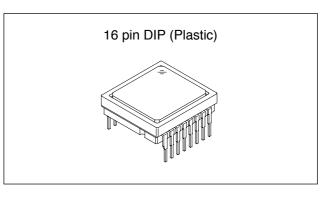
Features

- Progressive scan allows individual readout of the image signals from all pixels.
- High horizontal and vertical resolution (both approx. 768TV-lines) still image without a mechanical shutter.
- Supports high frame rate readout mode (effective 256 lines output, 15MHz drive: 45 frame/s, 20MHz drive: 60 frame/s)
- Square pixel
- Horizontal drive frequency: Typ.: 15MHz, Max.: 20MHz
- No voltage adjustments (reset gate and substrate bias are not adjusted.)
- · High resolution, high sensitivity, low dark current
- · Low smear, excellent antiblooming characteristics
- · Continuous variable-speed shutter
- Recommended range of exit pupil distance: -20 to -100mm

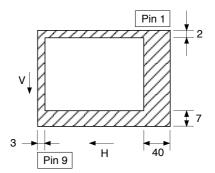
Device Structure

- Interline CCD image sensor
- Image size: Diagonal 6mm (Type 1/3) · Total number of pixels: 1077 (H) × 788 (V) approx. 850K pixels Number of effective pixels: 1034 (H) × 779 (V) approx. 800K pixels 1024 (H) × 768 (V) approx. 790K pixels (diagonal 5.952mm) · Number of active pixels: 5.80mm (H) × 4.92mm (V) Chip size: · Unit cell size: $4.65\mu m (H) \times 4.65\mu m (V)$ · Optical black: Horizontal (H) direction: Front 3 pixels, rear 40 pixels Vertical (V) direction: Front 7 pixels, rear 2 pixels Number of dummy bits: Horizontal 29 Vertical 1 · Substrate material: Silicon

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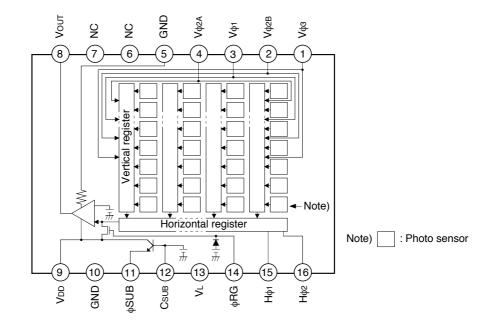
ICX204AL





Block Diagram and Pin Configuration

(Top View)



Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	Vфз	Vertical register transfer clock	9	VDD	Supply voltage
2	Vф2в	Vertical register transfer clock	10	GND	GND
3	Vφ1	Vertical register transfer clock	11	φSUB	Substrate clock
4	Vφ2Α	Vertical register transfer clock	12	Сѕив	Substrate bias*1
5	GND	GND	13	VL	Protective transistor bias
6	NC		14	φRG	Reset gate clock
7	NC		15	Ηφ1	Horizontal register transfer clock
8	Vout	Signal output	16	Ηφ2	Horizontal register transfer clock

*1 DC bias is generated within the CCD, so that this pin should be grounded externally through a capacitance of 0.1μ F.

Absolute Maximum Ratings

	Item	Ratings	Unit	Remarks
	Vdd, Vout, $\phi RG - \phi SUB$	-40 to +10	V	
Against _{\$SUB}	Vφ2Α, Vφ2Β – φSUB	-50 to +15	V	
	$V\phi_1, V\phi_3, V_L - \phi SUB$	-50 to +0.3	V	
	Hφ1, Hφ2, GND – φSUB	-40 to +0.3	V	
	Csub – фSUB	–25 to	V	
	Vdd, Vout, фRG, Csub – GND	-0.3 to +18	V	
Against GND	Vφ1, Vφ2Α, Vφ2Β, Vφ3 – GND	-10 to +18	V	
	Ηφ1, Ηφ2 – GND	-10 to +5	V	
Against GND Against V∟	Vφ2A, Vφ2B – VL	-0.3 to +28	V	
Against VL	Vφ1, Vφ3, Hφ1, Hφ2, GND – VL	-0.3 to +15	V	
	Voltage difference between vertical clock input pins	to +15	V	*2
•	Ηφ1 – Ηφ2	-5 to +5	V	
	Ηφ1, Ηφ2 – Vφ3	-13 to +13	V	
Storage temper	ature	-30 to +80	°C	
Operating temp	erature	-10 to +60	°C	

*2 +24V (Max.) when clock width < 10 μ s, clock duty factor < 0.1%.

+16V (Max.) is guaranteed for turning on or off power supply.

Bias Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	Vdd	14.55	15.0	15.45	V	
Protective transistor bias	VL		*1			
Substrate clock	φSUB		*2			
Reset gate clock	φRG		*2			

*1 VL setting is the VvL voltage of the vertical transfer clock waveform, or the same power supply as the VL power supply for the V driver should be used.

*2 Do not apply a DC bias to the substrate clock and reset gate clock pins, because a DC bias is generated within the CCD.

DC Characteristics

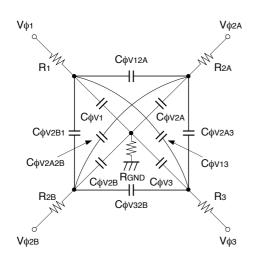
Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	Idd		5.5		mA	

Clock Voltage Conditions

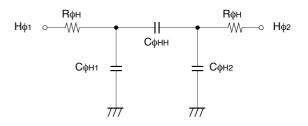
Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvт	14.55	15.0	15.45	V	1	
	Vvh02a	-0.05	0	0.05	V	2	Vvh = Vvho2a
Vertical transfer clock voltage	Vvh1, Vvh2a, Vvh2b, Vvh3	-0.2	0	0.05	V	2	
	Vvl1, Vvl2a, Vvl2b, Vvl3	-8	-7.5	-7	V	2	Vvl = (Vvl1 + Vvl3)/2
	Vφ1, Vφ2Α, Vφ2Β, Vφ3	7	7.5	8	V	2	
	I Vvl1 – Vvl3 I			0.1	V	2	
	Vvнн			0.9	V	2	High-level coupling
	Vvhl			1.3	V	2	High-level coupling
	Vvlh			1.0	V	2	Low-level coupling
	Vvll			0.9	V	2	Low-level coupling
Horizontal transfer	Vфн	3.0	3.3	3.6	V	3	
clock voltage	Vhl	-0.05	0	0.05	V	3	
	Vørg	3.0	3.3	3.6	V	4	
Reset gate clock voltage	Vrglh – Vrgll			0.4	V	4	Low-level coupling
voltago	Vrgl – Vrglm			0.5	V	4	Low-level coupling
Substrate clock voltage	Vφsub	21.55	22.5	23.45	V	5	

Clock Equivalent Circuit Constant

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
	C φV1		1500		pF	
Capacitance between vertical transfer clock and	C φν2Α		1800		pF	
GND	Сфv2в		1500 pF			
	Сфvз		2200		pF	pF
	СфV12А		390		pF	
	Сфv2B1		680		pF	
Capacitance between vertical transfer clocks	Сфизаз		560		pF	
Capacitance between vertical transfer clocks	Сфvз2в		1000		pF	
	СфV13		1800		pF	
	Сфv2а2в		33		pF	
Capacitance between horizontal transfer clock and GND	Сфн1, Сфн2		18		pF	
Capacitance between horizontal transfer clocks	Сфнн		43		pF	
Capacitance between reset gate clock and GND	Сфяд		3		pF	
Capacitance between substrate clock and GND	Сфѕив		390		pF	
	R1		91		Ω	
	R2A		68		Ω	
Vertical transfer clock series resistor	R2B		62		Ω	
	C ϕ v3CVeen vertical transfer clocksC ϕ v12ACC ϕ v2B1CCC ϕ v2A3CCC ϕ v32BCCC ϕ v13CCC ϕ v13CCVeen horizontal transfer clockC ϕ H1, C ϕ H2CVeen horizontal transfer clocksC ϕ HHCVeen reset gate clock and GNDC ϕ SUBCVeen substrate clock and GNDC ϕ SUBCR1CRR2BCRR3CRGND	30		Ω		
Vertical transfer clock ground resistor	Rgnd		43		Ω	
Horizontal transfer clock series resistor	Rфн		10		Ω	



Vertical transfer clock equivalent circuit

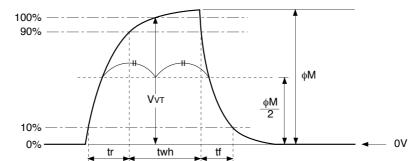


Horizontal transfer clock equivalent circuit

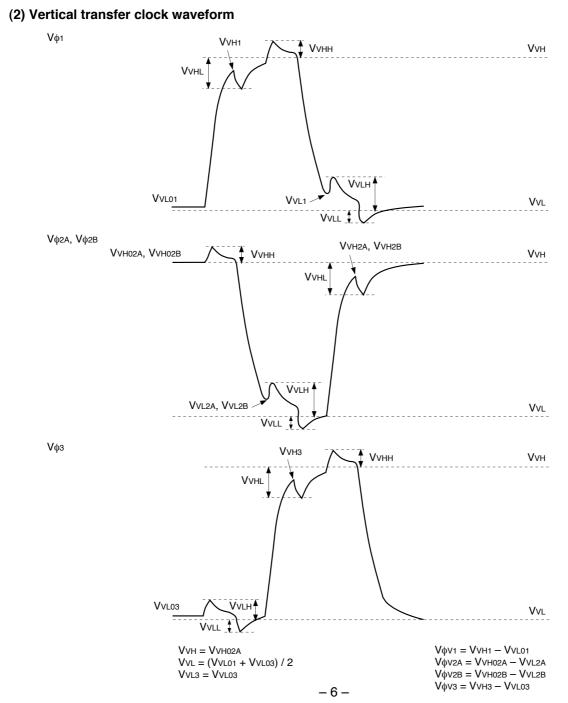
Drive Clock Waveform Conditions

(1) Readout clock waveform

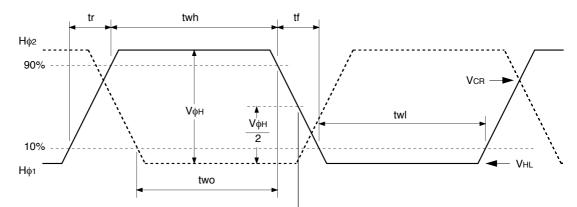




Note) Readout clock is used by composing vertical transfer clocks V ϕ _{2A} and V ϕ _{2B}.

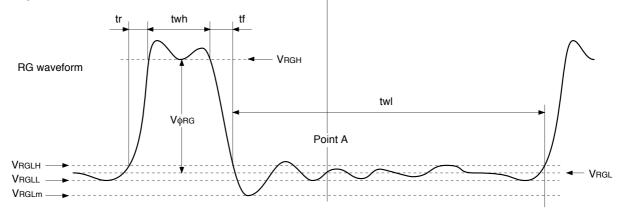


(3) Horizontal transfer clock waveform



Cross-point voltage for the H ϕ_1 rising side of the horizontal transfer clocks H ϕ_1 and H ϕ_2 waveforms is VCR. The overlap period for twh and twl of horizontal transfer clocks H ϕ_1 and H ϕ_2 is two.

(4) Reset gate clock waveform



VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG.

In addition, VRGL is the average value of VRGLH and VRGLL.

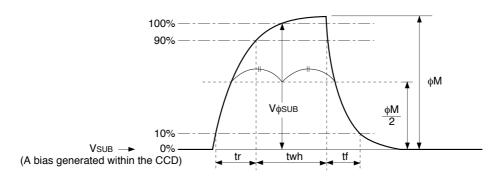
VRGL = (VRGLH + VRGLL)/2

Assuming VRGH is the minimum value during the interval twh, then:

Vørg = Vrgh – Vrgl.

Negative overshoot level during the falling edge of RG is VRGLm.

(5) Substrate clock waveform



Clock Switching Characteristics

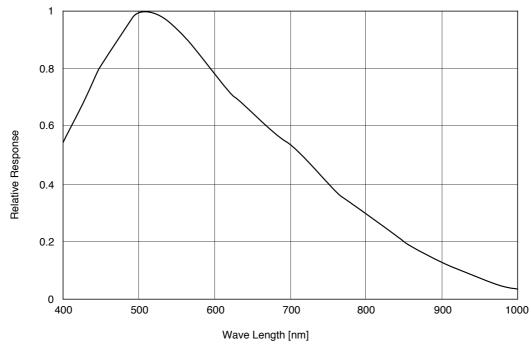
Item		Symbol	twh			twl			tr			tf		Unit	Remarks		
	nem	Symbol	Min.	Тур.	Max.		Tiemarko										
Rea	dout clock	Vτ	2.3	2.5						0.5			0.5		μs	During readout	
Ver cloc	tical transfer k	Vφ1, Vφ2Α, Vφ2Β, Vφ3										15		350	ns	*1	
풍 During	Hφ1	12.5	17		12.5	17			8	12.5		8	12.5	-	*2		
r clo		Ηφ2	12.5	17		12.5	17			8	12.5		8	12.5	ns		
Horizontal transfer cl	During	Hφ1					8.2			0.01			0.01				
Ho tra	parallel-serial conversion	Ηφ2		8.2						0.01			0.01		μs		
Res	et gate clock	φRG	7	10			34			3			3		ns		
Sub	strate clock	φSUB		2.2							0.5			0.5	μs	During drain charge	

*1 When vertical transfer clock driver CXD1267AN is used.

*2 tf ≥ tr – 2ns, and the cross-point voltage (VCR) for the Hφ1 rising side of the Hφ1 and Hφ2 waveforms must be at least VφH/2 [V].

Item	Symbol		two		Unit	Remarks	
nem	Symbol	Min.	Тур.	Max.	Unit		
Horizontal transfer clock	Ηφ1, Ηφ2	10.5	17		ns		

Spectral Sensitivity Characteristics (excludes lens characteristics and light source characteristics)

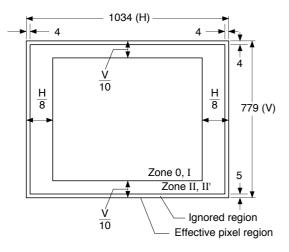


(Ta = 25°C)

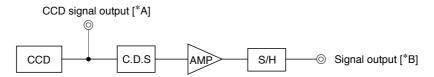
Image Sensor Characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity	S	360	450		mV	1	1/30s accumulation
Saturation signal	Vsat	450			mV	2	Ta = 60°C
Smear	Sm		0.001	0.004	%	3	No electronic shutter
	011			20	%	4	Zone 0 and I
Video signal shading	SH			25	%	4	Zone 0 to II'
Dark signal	Vdt			6	mV	5	Ta = 60°C, 20 frame/s
Dark signal shading	∆Vdt			2	mV	6	Ta = 60°C, 20 frame/s
Lag	Lag			0.5	%	7	

Zone Definition of Video Signal Shading



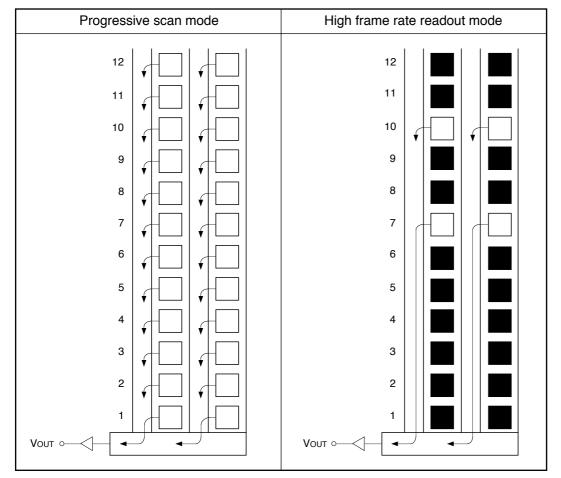
Measurement System



Note) Adjust the amplifier gain so that the gain between [*A] and [*B] equals 1.

Image Sensor Characteristics Measurement Method

Readout modes



The diagram below shows the output methods for the following two readout modes.

Note) Blacked out portions in the diagram indicate pixels which are not read out. Output starts from the line 7 in high frame rate readout mode.

1. Progressive scan mode

In this mode, all pixel signals are output in non-interlace format in 1/20s. The vertical resolution is approximately 768TV-lines and all pixel signals within the same exposure period are read out simultaneously, making this mode suitable for high resolution image capturing.

2. High frame rate readout mode

All effective areas are scanned in approximately 1/60s by reading out one line for every three lines. The vertical resolution is approximately 256TV-lines.

This readout mode emphasizes processing speed over vertical resolution.

◎ Measurement conditions

- 1) In the following measurements, the device drive conditions are at the typical values of the progressive scan mode, bias and clock voltage conditions.
- 2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black level (OB) is used as the reference for the signal output, which is taken as the value measured at point [*B] of the measurement system.

◎ Definition of standard imaging conditions

1) Standard imaging condition I:

Use a pattern box (luminance: 706cd/m², color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

2) Standard imaging condition II:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

3) Standard imaging condition III:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens (exit pupil distance -33mm) with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal outputs (Vs) at the center of screen, and substitute the values into the following formulas.

$$S = V_S \times \frac{250}{30} [mV]$$

2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 10 times the intensity with the average value of the signal output, 150mV, measure the minimum values of the signal output.

3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, first adjust the luminous intensity to 500 times the intensity with the average value of the signal output, 150mV. Then after the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value (V_{Sm} [mV]) of the signal output, and substitute the values into the following formula.

$$Sm = \frac{Vsm}{150} \times \frac{1}{500} \times \frac{1}{10} \times 100 \,[\%] \,(1/10V \text{ method conversion value})$$

4. Video signal shading

Set to standard imaging condition III. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 150mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output and substitute the values into the following formula.

SH = (Vmax – Vmin)/150 × 100 [%]

5. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

6. Dark signal shading

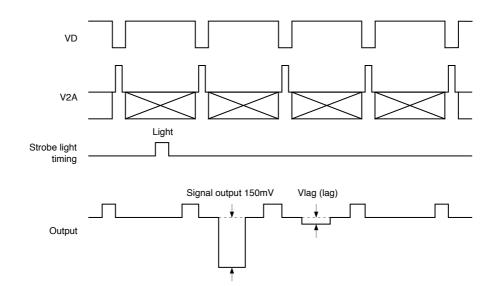
After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

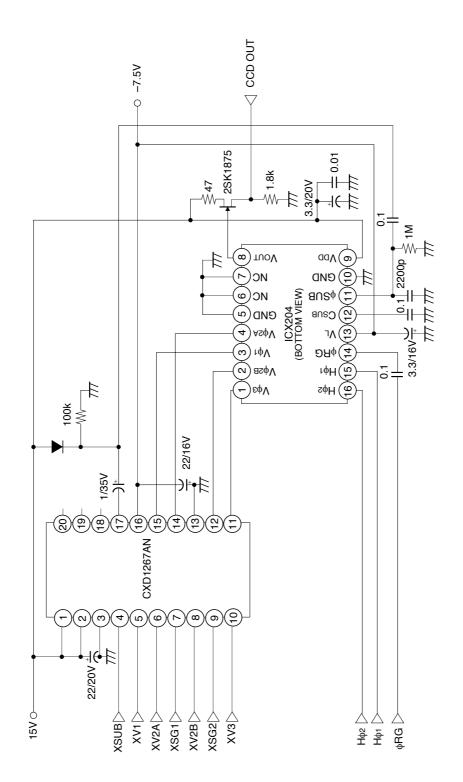
 $\Delta Vdt = Vdmax - Vdmin [mV]$

7. Lag

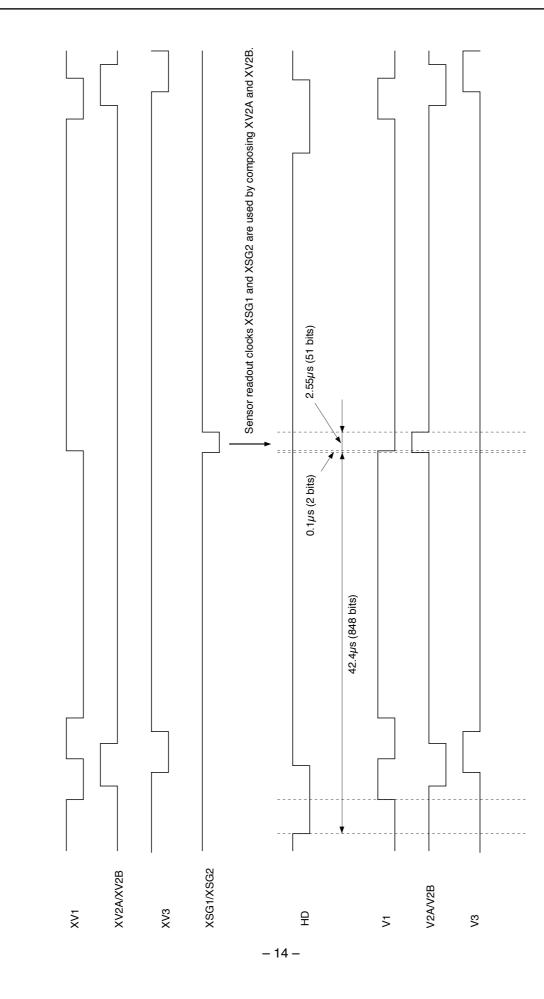
Adjust the signal output value generated by strobe light to 150mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

Lag = (Vlag/150) × 100 [%]





Drive Circuit

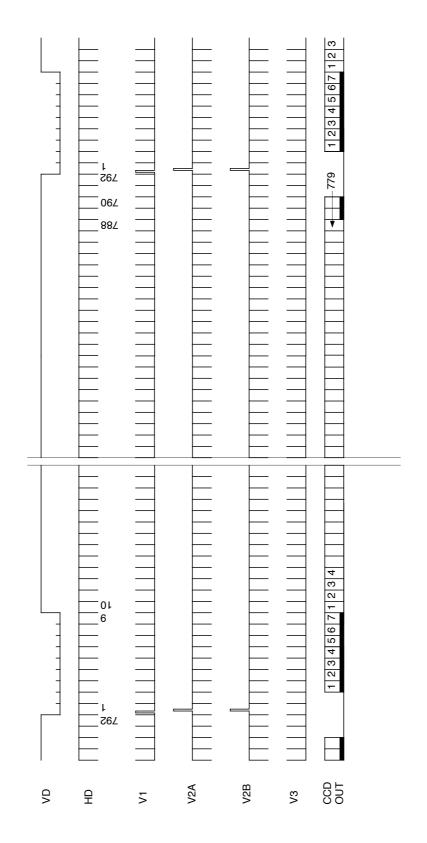


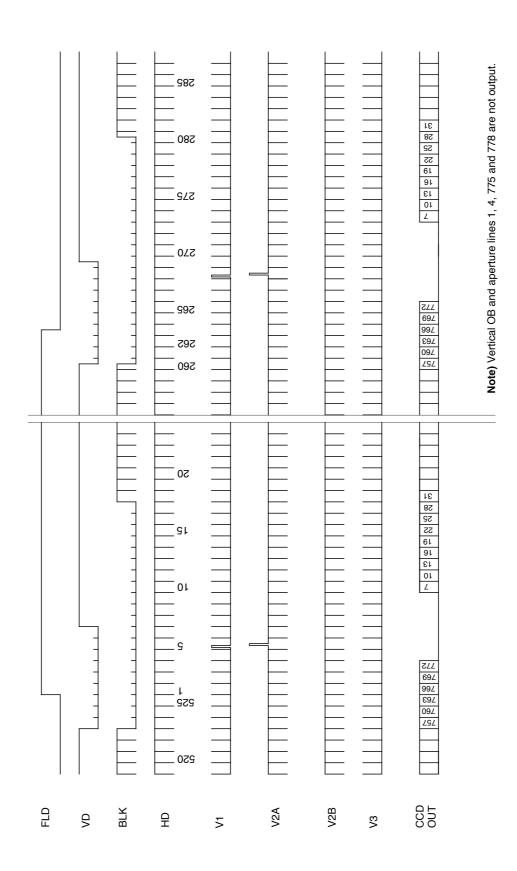
Sensor Readout Clock Timing Chart Progressive Scan Mode

High Frame Rate Readout Mode					Sensor readout clock XSG1 is used by composing XV2A.	0.1μs (2 bits) 0.1μs (2 bits) 2.55μs (51 bits) 2.7μs (54 bits) 2.7μs (54 bits)				5.0µs (100 bits) 5.0µs (100 bits) 10 bits 8 bits
Sensor Readout Clock Timing Chart High Frame Rate	XV1	XV2AXV2B	XV3	XSG1	XSG2	 HD 42.4µs (848 bits)	V1	V2A	V2B	

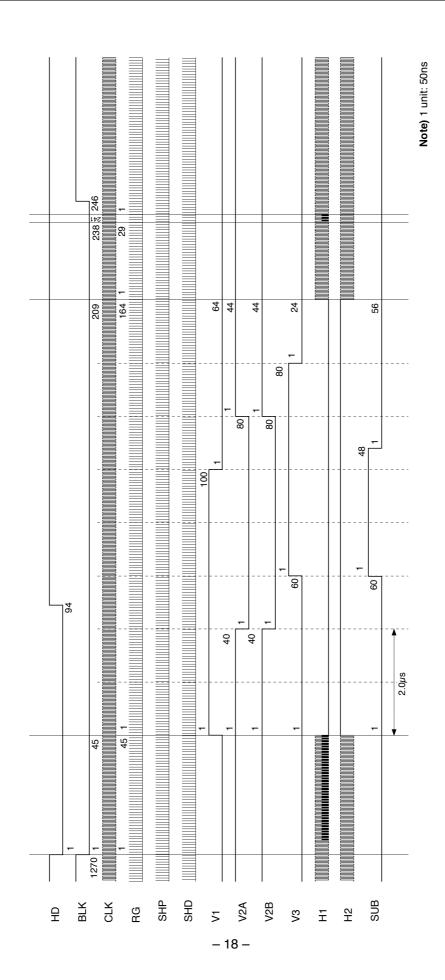
– 15 –



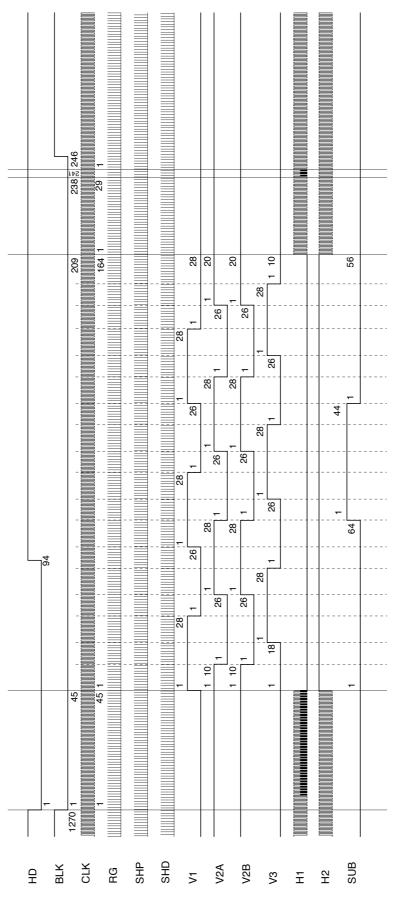




Progressive Scan Mode	
ng Chart (Horizontal Sync)	
Drive Timin	



High Frame Rate Readout Mode	
Drive Timing Chart (Horizontal Sync)	



Note) 1 unit: 50 ns

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Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

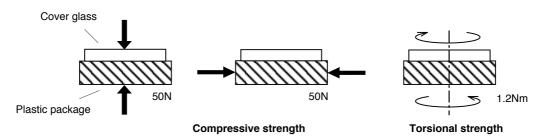
- a) Either handle bare handed or use non-chargeable gloves, clothes or material.
 - Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) lonized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a ground 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.
- 3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Perform all assembly operations in a clean room (class 1000 or less).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.
- 4) Installing (attaching)
 - a) Remain within the following limits when applying a static load to the package. Do not apply any load more than 0.7mm inside the outer perimeter of the glass portion, and do not apply any load or impact to limited portions. (This may cause cracks in the package.)

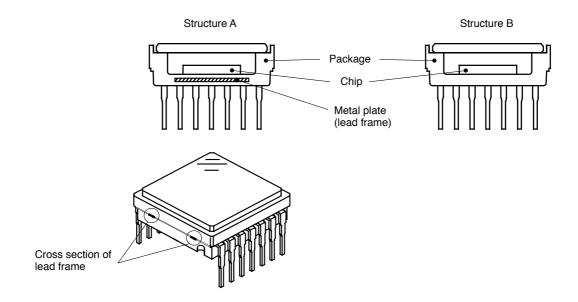


b) If a load is applied to the entire surface by a hard component, bending stress may be generated and the package may fracture, etc., depending on the flatness of the bottom of the package. Therefore, for installation, use either an elastic load, such as a spring plate, or an adhesive.

- c) The adhesive may cause the marking on the rear surface to disappear, especially in case the regulated voltage value is indicated on the rear surface. Therefore, the adhesive should not be applied to this area, and indicated values should be transferred to the other locations as a precaution.
- d) The notch of the package is used for directional index, and that can not be used for reference of fixing. In addition, the cover glass and seal resin may overlap with the notch of the package.
- e) If the lead bend repeatedly and the metal, etc., clash or rub against the package, the dust may be generated by the fragments of resin.
- f) Acrylate anaerobic adhesives are generally used to attach CCD image sensors. In addition, cyanoacrylate instantaneous adhesives are sometimes used jointly with acrylate anaerobic adhesives. (reference)

5) Others

- a) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
- b) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.
- c) The brown stain may be seen on the bottom or side of the package. But this does not affect the CCD characteristics.
- d) This package has 2 kinds of internal structure. However, their package outline, optical size, and strength are the same.



The cross section of lead frame can be seen on the side of the package for structure A.

	9 6 11.6 11.6 11.6 11.6 2-R0.5	"A" is the center of the effective image area. The two points "B" of the package are the horizontal reference. The point "B" of the package is the vertical reference.	The bottom "C" of the package, and the top of the cover glass "D" are the height reference. The center of the effective image area relative to "B" and "B" $(H, V) = (6.1, 5.7) \pm 0.15$ mm.	The rotation angle of the effective image area relative to H and V is \pm 1°. The height from the bottom "C" to the effective image area is 1.41 \pm 0.10mm. The height from the top of the cover glass "D" to the effective image area is 1.94 \pm 0.15mm.	The tilt of the effective image area relative to the bottom "C" is less than 50μ m.	The tilt of the effective image area relative to the top "D" of the cover glass is less than 50µm.	The thickness of the cover glass is 0.75mm, and the refractive index is 1.5.	The notches on the bottom of the package are used only for directional index, they must	
(450mil)	0.52 0.00 0.00 0.00 0.00 0.00 0.00 0.00					The tilt of the effecti	•	• •	
16 pin DIP (450mil)	2.35 ± 0.15 	3.1	0.3 0.46 0.3 0.46 0.3 0.5 ± 0.3 0.4 0.3	່ວ ວ 3	7.		α	б	
Package Outline Unit: mm	6.1 10.3 12.2 ± 0.1			⊕ 0.3 @ RE	Plastic	GOLD PLATING	42 ALLOY	0.90g	AS-C2.2-01(E)
	0.5 5.7 5.7 5.7 5.7		0.69 (For the first pin only)	PACKAGE STRUCTURE	PACKAGE MATERIAL	LEAD TREATMENT	LEAD MATERIAL	PACKAGE MASS	DRAWING NUMBER
Pack		_ 22 _		<u> </u>			<u> </u>	Sor	

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